

Po-Chun Chang

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/2437094/publications.pdf>

Version: 2024-02-01

12
papers

149
citations

1307594

7
h-index

1588992

8
g-index

12
all docs

12
docs citations

12
times ranked

224
citing authors

#	ARTICLE	IF	CITATIONS
1	Normally-Off Tri-Gate GaN MIS-HEMTs with $0.76 \text{ m}\Omega\text{-cm}^2$ Specific On-Resistance for Power Device Applications. IEEE Transactions on Electron Devices, 2019, 66, 3441-3446.	3.0	26
2	High-Performance Normally-OFF GaN MIS-HEMTs Using Hybrid Ferroelectric Charge Trap Gate Stack (FEG-HEMT) for Power Device Applications. IEEE Electron Device Letters, 2018, 39, 991-994.	3.9	35
3	Normally-OFF GaN MIS-HEMT With δ -Doped Gate Insulator Using Standard Ion Implantation. IEEE Journal of the Electron Devices Society, 2018, 6, 893-899.	2.1	29
4	InGaAs Junctionless FinFETs with Self-Aligned Ni-InGaAs S/D. IEEE Journal of the Electron Devices Society, 2018, , 1-1.	2.1	10
5	InGaAs QW-MOSFET Performance Improvement Using a PEALD-AlN Passivation Layer and an <i>In-Situ</i> NH ₃ Post Remote-Plasma Treatment. IEEE Electron Device Letters, 2017, 38, 310-313.	3.9	4
6	High-Performance GaN MOSHEMTs Fabricated With ALD Al ₂ O ₃ Dielectric and NBE Gate Recess Technology for High Frequency Power Applications. IEEE Electron Device Letters, 2017, 38, 771-774.	3.9	21
7	Corrections to "AlGaIn/GaN HEMTs With Damage-Free Neutral Beam Etched Gate Recess for High-Performance Millimeter-Wave Applications" [Nov 16 1395-1398]. IEEE Electron Device Letters, 2017, 38, 149-149.	3.9	0
8	HfO ₂ /AlN/In _{0.53} Ga _{0.47} As MOS devices electrical properties and reliability studies. , 2016, , .		0
9	Study on the electrical characteristics of in situ PEALD-passivated HfO ₂ /In _{0.53} Ga _{0.47} As MOSCAP and MOSFET structures. , 2016, , .		0
10	Electrical Analysis and PBTI Reliability of In _{0.53} Ga _{0.47} As MOSFETs With AlN Passivation Layer and NH ₃ Postremote Plasma Treatment. IEEE Transactions on Electron Devices, 2016, 63, 3466-3472.	3.0	8
11	AlGaIn/GaN HEMTs With Damage-Free Neutral Beam Etched Gate Recess for High-Performance Millimeter-Wave Applications. IEEE Electron Device Letters, 2016, 37, 1395-1398.	3.9	16
12	In _x Ga _{1-x} As materials for post CMOS application: Materials and device aspects. , 2014, , .		0